

POWERED BY **Dialog****MANUFACTURE OF THIN FILM TRANSISTOR (08-032085****Publication Number:** JP 8032085 A) , February 02, 1996**Inventors:**

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- H01L-029/786
- H01L-021/336
- C23C-016/44
- C23C-018/12
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- G02F-001/136
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JAPIO Class:

- 42.2 (ELECTRONICS--- Solid State Components)
- 12.6 (METALS--- Surface Treatment)
- 13.1 (INORGANIC CHEMISTRY--- Processing Operations)
- 29.2 (PRECISION INSTRUMENTS--- Optical Equipment)
- 44.9 (COMMUNICATION--- Other)

JAPIO Keywords:

- R002 (LASERS)
- R004 (PLASMA)
- R011 (LIQUID CRYSTALS)
- R096 (ELECTRONIC MATERIALS--- Glass Conductors)

Abstract:

PURPOSE: To form a silicon thin film easily and reliably by a method wherein a silicon thin film, which is used as a channel semiconductor film, is coated with a specified liquid silicon hydride film and thereafter, is made to have a heat history comprising a heat-up process and is made to decompose within the applied film.

CONSTITUTION: A silicon thin film used as a channel semiconductor film is coated with a liquid silicon hydride film containing an $\text{Si}(\text{sub } m)\text{H}(\text{sub } 2)m+2$ or $\text{Si}(\text{sub } n)\text{H}(\text{sub } 2)n$ (provided that the (m) and the (n) are such an integer

as to satisfy each condition of $m \geq 5$ and $n \geq 4$.) on a substrate 105 and thereafter, is heated up by a heating means, is made to have a heat history comprising a heat-up process, is made to decompose in the applied film and a silicon thin film to satisfy characteristics requisite as a TFT material is formed on the substrate 105. Thereby, the silicon thin film can be formed easily and reliably.

JAPIO

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